



SDI Review Form 1.6

Journal Name:	Physical Science International Journal
Manuscript Number:	2015_PSIJ_18362
Title of the Manuscript:	Diffusion and trapping of positrons in unimplanted and ion-implanted 3C-SiC and 6H-SiC
Type of the Article	Original Research Article

General guideline for Peer Review process:

This journal's peer review policy states that **NO** manuscript should be rejected only on the basis of '**lack of Novelty**', provided the manuscript is scientifically robust and technically sound.

To know the complete guideline for Peer Review process, reviewers are requested to visit this link:

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PART 1: Review Comments

	Reviewer's comment	Author's comment <i>(if agreed with reviewer, correct the manuscript and highlight that part in the manuscript. It is mandatory that authors should write his/her feedback here)</i>
<u>Compulsory</u> REVISION comments		
<u>Minor</u> REVISION comments	<p>It is necessary to add in the Introduction session two references on the papers, where SiC materials were explored using positron annihilation (materials, implanted by Al- ions with five different energies). The authors found there the forming of divacancies with lifetime equal to 218 and 216 ps etc.</p> <p>The references:</p> <ol style="list-style-type: none"> 1. Trifthauser W. in Proc. Of the Intern. Workshop on Advanced Techniques of Positron Beam Generation and Control JAERI, Japan, 1998, p. 57. 2. A.D. Pogrebnjak, A.G. Ponomarev, A.P. Shpak, Yu.A. Kunitskii. Application of micro-nanoprobes to the analysis of small-size 3D materials, nanosystems and nanoobjects. Phys. Uspekhi 55 (3), 270 – 300, 2012. 	<p>Few new references added in introduction part along with these two suggested references, especially to demonstrate the dependence of the mean positron lifetime in p-type SiC after Al+ implantation and subsequent annealing on mean implantation depth. Also to discuss the saturated positron lifetime (218 ps) observed (216 ps calculated) in SiC implanted with Al+ at positron implantation energies for 2 to ~ 10 KeV.</p>
<u>Optional/General</u> comments	<p>General level of the paper is rather good. It can be published in the Journal with minor corrections.</p>	<p>Manuscript modified as per suggestions.</p>